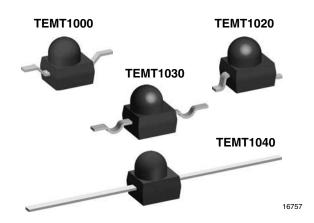
Vishay Semiconductors



Silicon NPN Phototransistor, RoHS Compliant



DESCRIPTION

TEMT1000 series are silicon NPN phototransistors with high radiant sensitivity in black, surface mount, plastic packages with lens and daylight blocking filter. Filter bandwidth is matched with 870 nm to 950 nm IR emitters.

FEATURES

- · Package type: surface mount
- · Package form: GW, RGW, yoke, axial
- Dimensions (L x W x H in mm): 2.5 x 2 x 2.7
- · High radiant sensitivity
- Daylight blocking filter matched with 870 nm to 950 nm IR emitters



- Fast response times
- Angle of half sensitivity: $\varphi = \pm 15^{\circ}$
- Package matches with IR emitter series TSML1000
- Floor life: 168 h, MSL 3, acc. J-STD-020
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

APPLICATIONS

- · Detector in electronic control and drive circuits
- · IR detector for daylight application
- · Photo interrupters
- Counter
- Encoder

PRODUCT SUMMARY			
COMPONENT	I _{ca} (mA)	φ (deg)	λ _{0.5} (nm)
TEMT1000	7	± 15	730 to 1000
TEMT1020	7	± 15	730 to 1000
TEMT1030	7	± 15	730 to 1000
TEMT1040	7	± 15	730 to 1000

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	PACKAGING	REMARKS PACKAGE		
TEMT1000	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Reverse gullwing	
TEMT1020	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Gullwing	
TEMT1030	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Yoke	
TEMT1040	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	Axial leads	

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Emitter collector voltage		V _{ECO}	5	V	
Collector current		I _C	50	mA	
Collector peak current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I _{CM}	100	mA	
Power dissipation	T _{amb} ≤ 55 °C	P_V	100	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T _{amb}	- 40 to + 85	°C	
Storage temperature range		T _{stg}	- 40 to + 100	°C	
Soldering temperature	t ≤ 5 s	T _{sd}	260	°C	
Thermal resistance junction/ambient	Soldered on PCB with pad dimensions: 4 mm x 4 mm	R _{thJA}	400	K/W	

Note

T_{amb} = 25 °C, unless otherwise specified

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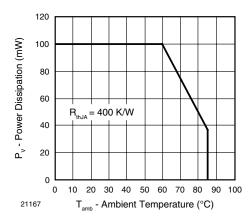


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector emitter voltage	I _C = 1 mA	V _{CEO}	70			V
Collector emitter dark current	$V_{CE} = 20 \text{ V}, E = 0$	I _{CEO}		1	200	nA
Collector emitter capacitance	V _{CE} = 5 V, f = 1 MHz, E = 0	C _{CEO}		3		pF
Angle of half sensitivity		φ		± 15		deg
Wavelength of peak sensitivity		λ_{p}		880		nm
Range of spectral bandwidth		λ _{0.5}		730 to 1000		nm
Collector emitter saturation voltage	$E_{e} = 1 \text{ mW/cm}^{2}, \lambda = 950 \text{ nm},$ $I_{C} = 0.1 \text{ mA}$	V _{CEsat}			0.3	V
Turn-on time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	t _{on}		2.0		μs
Turn-off time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	t _{off}		2.3		μs
Cut-off frequency	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	f _c		180		kHz
Collector light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm},$ $V_{CE} = 5 \text{ V}$	I _{ca}	2	7.0		mA

Note

T_{amb} = 25 °C, unless otherwise specified

BASIC CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

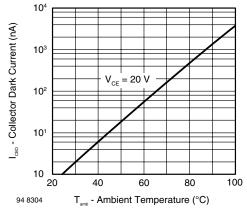


Fig. 2 - Collector Dark Current vs. Ambient Temperature

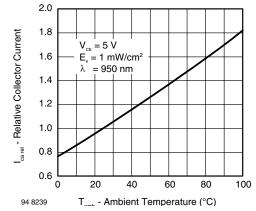


Fig. 3 - Relative Collector Current vs. Ambient Temperature

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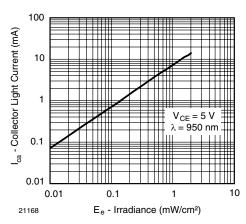


Fig. 4 - Collector Light Current vs. Irradiance

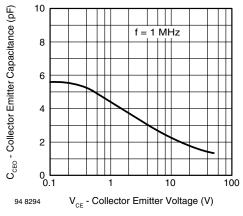


Fig. 5 - Collector Emitter Capacitance vs. Collector Emitter Voltage

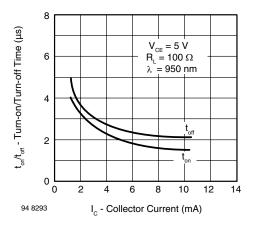


Fig. 6 - Turn-on/Turn-off Time vs. Collector Current

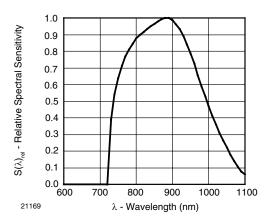


Fig. 7 - Relative Spectral Sensitivity vs. Wavelength

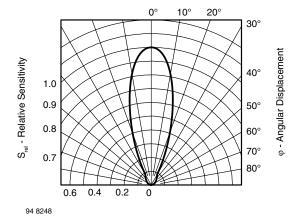


Fig. 8 - Relative Radiant Sensitivity vs. Angular Displacement

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PRECAUTIONS FOR USE

1. Over-current-proof

Customer must apply resistors for protection, otherwise slight voltage shift will cause big current change (burn out will happen).

2. Storage

- 2.1 Storage temperature and rel. humidity conditions are: 5 °C to 35 °C, R.H. 60 %.
- 2.2 Floor life must not exceed 168 h, acc. to JEDEC level 3, J-STD-020.
 - Once the package is opened, the products should be used within a week. Otherwise, they should be kept in a damp proof box with desiccant.
 - Considering tape life, we suggest to use products within one year from production date.
- 2.3 If opened more than one week in an atmosphere 5 °C to 35 °C, R.H. 60 %, devices should be treated at 60 °C \pm 5 °C for 15 h.
- 2.4 If humidity indicator in the package shows pink color (normal blue), then devices should be treated with the same conditions as 2.3.

REFLOW SOLDER PROFILE

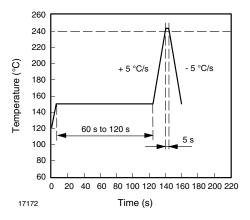
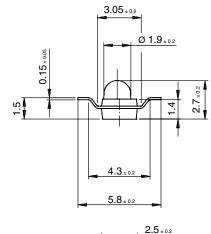
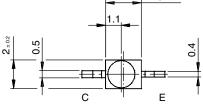


Fig. 9 - Lead Tin (SnPb) Reflow Solder Profile

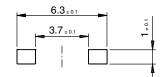
PACKAGE DIMENSIONS in millimeters: **TEMT1000**





technical drawings according to DIN specifications

Solder pad proposal



Drawing-No.: 6.544-5326.01-4

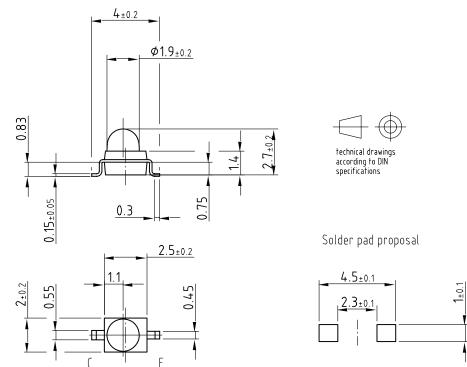
Issue: 4; 02.04.03

16104

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PACKAGE DIMENSIONS in millimeters: TEMT1020

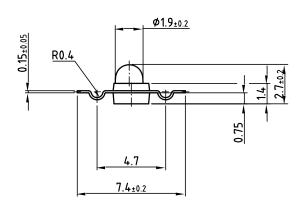


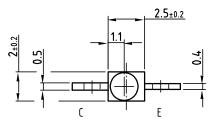
Drawing-No.: 6.544-5325.01-4

Issue: 5; 19.01.06

16105

PACKAGE DIMENSIONS in millimeters: **TEMT1030**

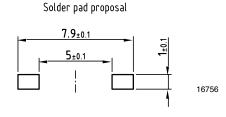




Drawing-No.: 6.544-5329.02-4 Issue: 3; 08.05.03

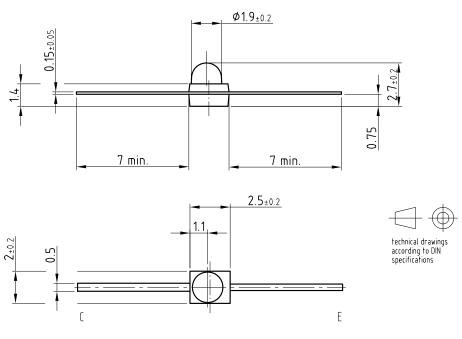


All dimensions in mm



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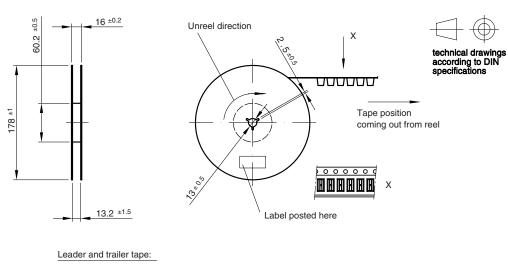
PACKAGE DIMENSIONS in millimeters: **TEMT1040**

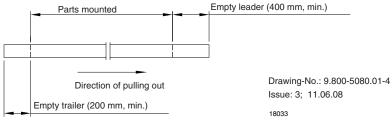


Drawing-No.: 6.544-5339.01-4

Issue: 2; 02.04.03

REEL DIMENSIONS in millimeters

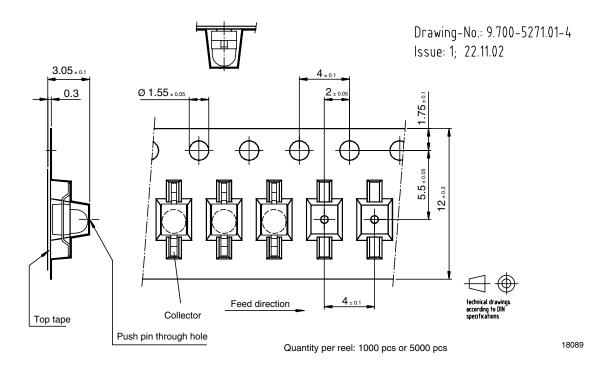




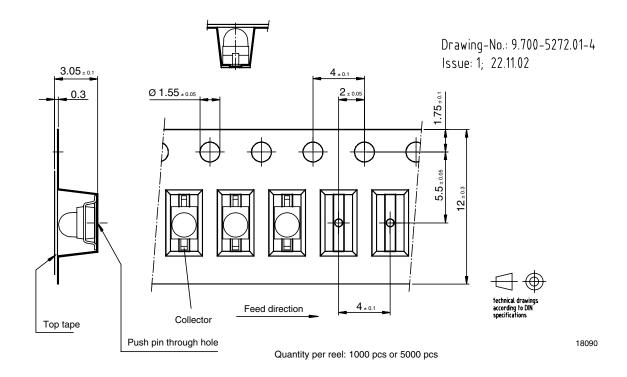
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TAPING DIMENSIONS in millimeters: **TEMT1000**

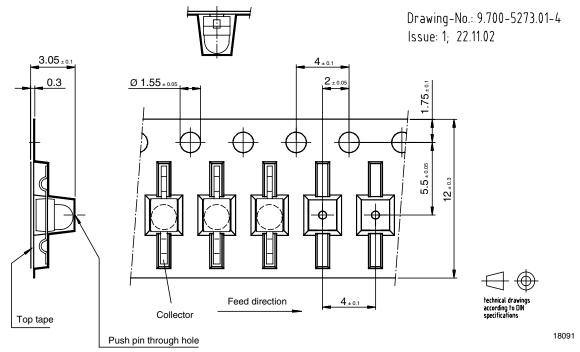


TAPING DIMENSIONS in millimeters: **TEMT1020**



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TAPING DIMENSIONS in millimeters: **TEMT1030**





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